

Rapidly fabricating large area nanotip microstructure for high-sensitivity SERS applications

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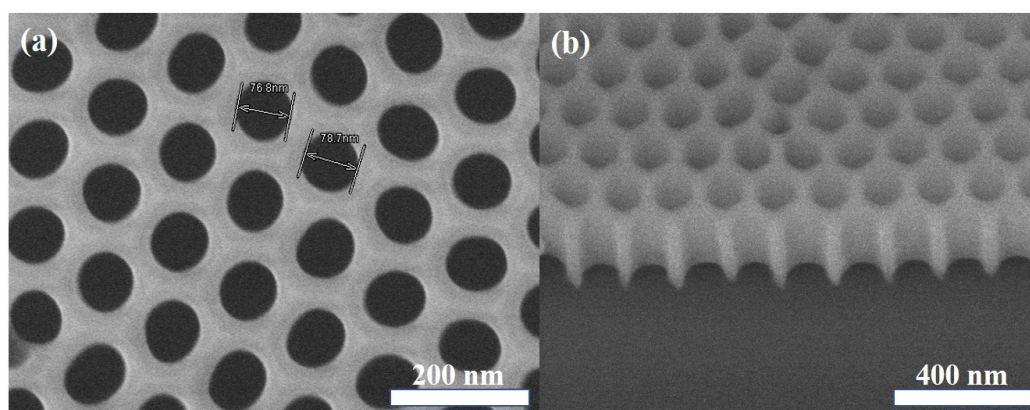


Fig. S1 SEM images of AAO template.

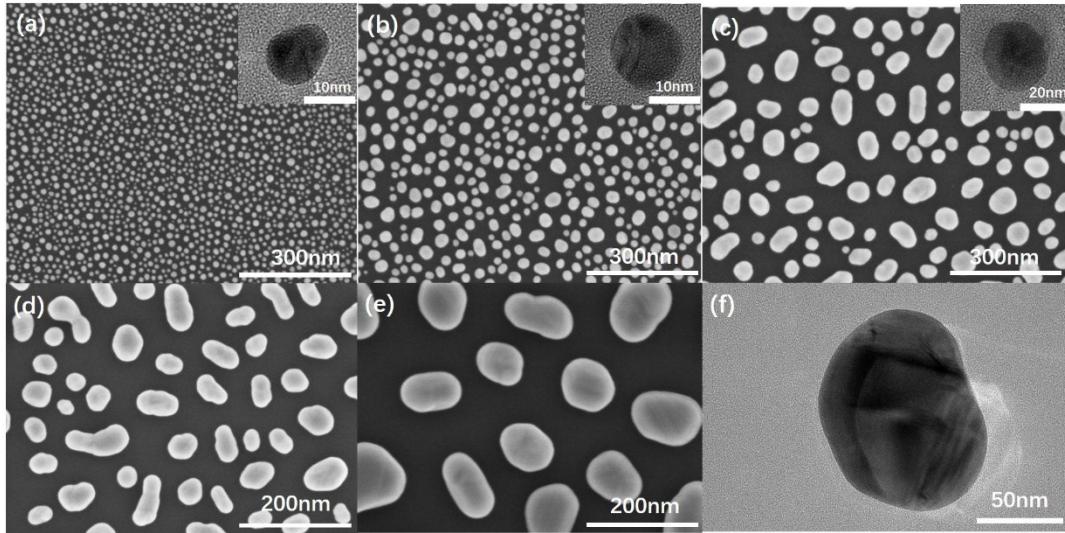


Fig. S2 SEM and TEM images of Ag particles under different Ag film thicknesses after annealing. (a)-(e): 3 nm, 6 nm, 9 nm, 12 nm, 15 nm. The enlarged images are corresponding TEM images. (f) TEM image of Ag particle with 15 nm Ag film after annealing.

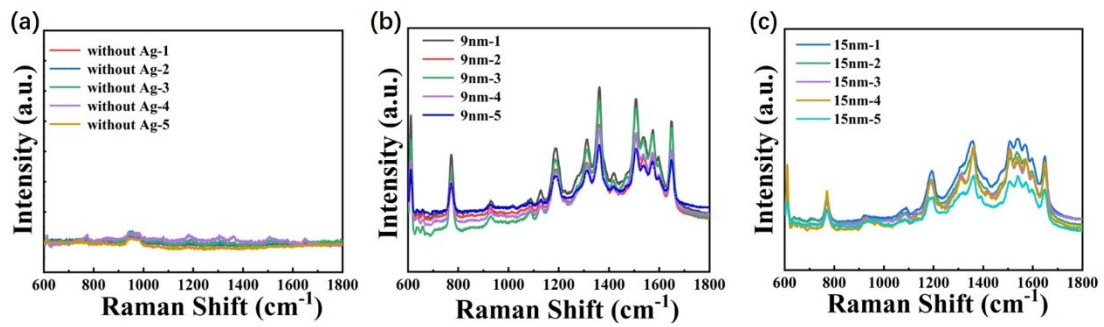


Fig. S3 The Raman spectra of R6G molecules collected at several sites randomly from Si substrate.